# onsemi

## **MOSFET** – N-Channel, POWERTRENCH<sup>®</sup>

100 V, 300 A, 2.0 m $\Omega$ 

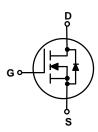
## FDBL86062-F085

#### Features

- Typical  $R_{DS(on)} = 1.5 \text{ m}\Omega$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 80 \text{ A}$
- Typical  $Q_{g(tot)} = 95 \text{ nC}$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 80 \text{ A}$
- UIS Capability
- Qualified to AEC Q101
- This Device is Pb–Free and is RoHS Compliant

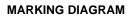
#### Applications

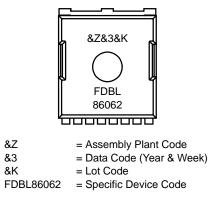
- Automotive Engine Control
- PowerTrain Management
- Solenoid and Motor Drivers
- Integrated Starter/Alternator
- Primary Switch for 12 V Systems





H-PSOF8L 11.68x9.80 CASE 100CU





#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

#### **MOSFET MAXIMUM RATINGS** $T_J = 25^{\circ}C$ unless otherwise noted

| Symbol                            | Parameter  | Parameter           |              | Units |
|-----------------------------------|--|---------------------|--------------|-------|
| V <sub>DSS</sub>                  | Drain-to-Source Voltage                                    |                     | 100          | V     |
| V <sub>GS</sub>                   | Gate-to-Source Voltage                                     |                     | ±20          | V     |
| Ι <sub>D</sub>                    | Drain Current - Continuous (V <sub>GS</sub> = 10) (Note 1) | $T_C = 25^{\circ}C$ | 300          | А     |
|                                   | Pulsed Drain Current                                       | $T_C = 25^{\circ}C$ | See Figure 4 |       |
| E <sub>AS</sub>                   | Single Pulse Avalanche Energy (Note 2)                     |                     | 352          | mJ    |
| PD                                | Power Dissipation  |                     | 429          | W     |
|                                   | Derate Above 25°C  |                     | 2.9          | W/°C  |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature                          |                     | -55 to +175  | °C    |
| $R_{	extsf{	heta}JC}$             | Thermal Resistance, Junction to Case                       |                     | 0.35         | °C/W  |
| $R_{\thetaJA}$                    | Maximum Thermal Resistance, Junction to Ambient (Note 3)   |                     | 43           | °C/W  |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Current is limited by silicon.
Starting T<sub>J</sub> = 25°C, L = 0.1 mH, I<sub>AS</sub> = 84 A, V<sub>DD</sub> = 100 V during inductor charging and V<sub>DD</sub> = 0 V during time in avalanche.
R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design, while R<sub>θJA</sub> is determined by the board design. The maximum rating presented here is based on mounting on a 1 in<sup>2</sup> pad of 2oz copper.

#### PACKAGE MARKING AND ORDERING INFORMATION

| Device Marking | Device         | Package  | Reel Size | Tape Width | Quantity   |
|----------------|----------------|----------|-----------|------------|------------|
| FDBL86062      | FDBL86062-F085 | H-PSOF8L | 13"       | 24 mm      | 2000 Units |

#### **ELECTRICAL CHARACTERISTICS** $T_J = 25^{\circ}C$ , unless otherwise noted

| Symbol              | Parameter                         |                                 | Test Conditions                 | Min. | Тур. | Max. | Units |  |
|---------------------|-----------------------------------|---------------------------------|---------------------------------|------|------|------|-------|--|
| OFF CHARACTERISTICS |                                   |                                 |                                 |      |      |      |       |  |
| B <sub>VDSS</sub>   | Drain-to-Source Breakdown Voltage | $I_D = 250 \ \mu A, \ V_{GS} =$ | = 0 V                           | 100  | _    | -    | V     |  |
| I <sub>DSS</sub>    | Drain-to-Source Leakage Current   | $V_{GS} = 0 V$                  | $T_J = 25^{\circ}C$             | -    | -    | 5    | μΑ    |  |
|                     |                                   |                                 | T <sub>J</sub> = 175°C (Note 4) | -    | -    | 2    | mA    |  |
| I <sub>GSS</sub>    | Gate-to-Source Leakage Current    | $V_{GS} = \pm 20 V$             |                                 | _    | _    | ±100 | nA    |  |
| IGSS                |                                   |                                 | <u> </u>                        | -    | -    | ÷    | 2     |  |

#### **ON CHARACTERISTICS**

| V <sub>GS(th)</sub> | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250 \ \mu A$ |                                 | 2.0 | 3.1 | 4.5 | V  |
|---------------------|----------------------------------|--------------------------------------|---------------------------------|-----|-----|-----|----|
| R <sub>DS(on)</sub> | Drain to Source On Resistance    | $I_{\rm D} = 80  \rm A,$             | $T_J = 25^{\circ}C$             | -   | 1.5 | 2.0 | mΩ |
|                     |                                  | V <sub>GS</sub> = 10 V               | T <sub>J</sub> = 175°C (Note 4) | _   | 3.3 | 4.3 |    |

#### DYNAMIC CHARACTERISTICS

| C <sub>iss</sub>    | Input Capacitance             | $V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V},$  |                       | - | 6970 | -   | pF |
|---------------------|-------------------------------|---|-----------------------|---|------|-----|----|
| C <sub>oss</sub>    | Output Capacitance            | T = 1 MHZ   | f = 1 MHz             |   | 3950 | -   |    |
| C <sub>rss</sub>    | Reverse Transfer Capacitance  | The second se |                       | - | 29   | -   |    |
| Rg                  | Gate Resistance               | f = 1 MHz   |                       | - | 0.4  | -   | Ω  |
| Q <sub>g(ToT)</sub> | Total Gate Charge at 10 V     | $V_{GS} = 0$ to 10 V  | $V_{DD} = 80 V$       | - | 95   | 124 | nC |
| Q <sub>g(th)</sub>  | Threshold Gate Charge         | $V_{GS} = 0$ to 2 V   | I <sub>D</sub> = 80 A | - | 13   | -   |    |
| Q <sub>gs</sub>     | Gate-to-Source Gate Charge    |   |                       | - | 31   | -   |    |
| Q <sub>gd</sub>     | Gate-to-Drain "Miller" Charge |   |                       | - | 20   | -   |    |

#### **ELECTRICAL CHARACTERISTICS** (continued) $T_J = 25^{\circ}C$ , unless otherwise noted

| Symbol                            | Parameter      |   | Test Conditions                     | Min. | Тур. | Max. | Units |  |  |  |
|-----------------------------------|----------------|---|-------------------------------------|------|------|------|-------|--|--|--|
| SWITCHING CHARACTERISTICS         |                |   |                                     |      |      |      |       |  |  |  |
| t <sub>on</sub>                   | Turn–On Time   | $V_{DD} = 50 \text{ V}, \text{ I}_{D} = 80 \text{ V}_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 10 \text{ V}$ | A,                                  | -    | -    | 73   | ns    |  |  |  |
| t <sub>d(on)</sub>                | Turn–On Delay  | $V_{GS} = 10 V, R_{GEN}$  | $V_{GS} = 10 V, R_{GEN} = 6 \Omega$ | -    | 31   | -    |       |  |  |  |
| t <sub>r</sub>                    | Rise Time      |   |                                     | -    | 25   | -    |       |  |  |  |
| t <sub>d(off)</sub>               | Turn–Off Delay |   |                                     | -    | 36   | -    |       |  |  |  |
| t <sub>f</sub>                    | Fall Time      |   |                                     | -    | 9    | -    |       |  |  |  |
| t <sub>off</sub>                  | Turn-Off Time  | 7   |                                     | -    | -    | 59   |       |  |  |  |
| RAIN-SOURCE DIODE CHARACTERISTICS |                |   |                                     |      |      |      |       |  |  |  |

| $V_{SD}$        | Source-to-Drain Diode Voltage | $I_{SD} = 80 \text{ A}, V_{GS} = 0 \text{ V}$          | - | _   | 1.25 | V  |
|-----------------|-------------------------------|--|---|-----|------|----|
|                 |                               | $I_{SD} = 40 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$  | - | -   | 1.2  |    |
| t <sub>rr</sub> | Reverse–Recovery Time         | $I_F$ = 80 A, $dI_{SD}/dt$ = 100 A/µs, $V_{DD}$ = 80 V | - | 115 | 150  | ns |
| Q <sub>rr</sub> | Reverse–Recovery Charge       |  | _ | 172 | 224  | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. The maximum value is specified by design at  $T_J = 175^{\circ}$ C. Product is not tested to this condition in production.

#### **TYPICAL CHARACTERISTICS**

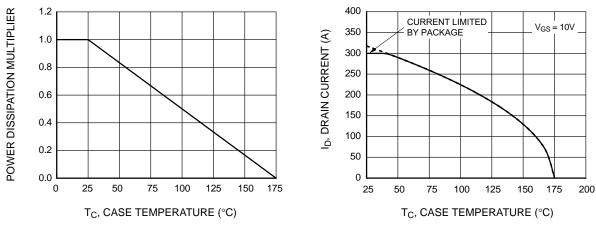


Figure 1. Normalized Power Dissipation vs. Case Temperature

Figure 2. Maximum Continuous Drain Current vs. Case Temperature

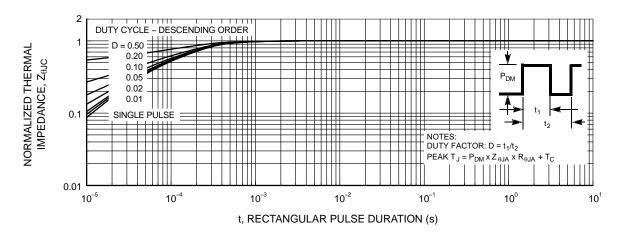
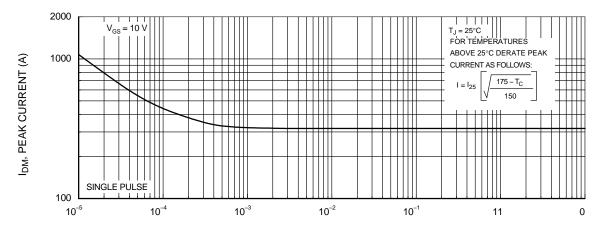


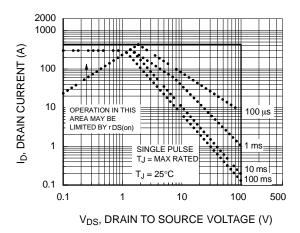
Figure 3. Normalized Maximum Transient Thermal Impedance



t, RECTANGULAR PULSE DURATION (s)

Figure 4. Peak Current Capability

#### TYPICAL CHARACTERISTICS (CONTINUED)







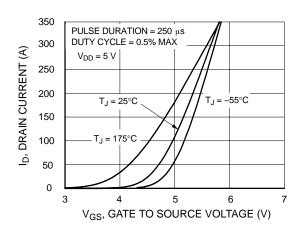


Figure 7. Transfer Characteristics

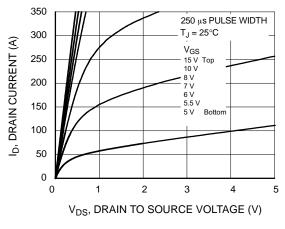


Figure 9. Saturation Characteristics

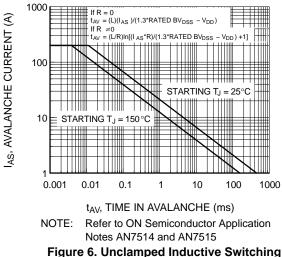


Figure 6. Unclamped inductive Switching Capability

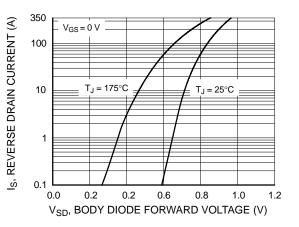
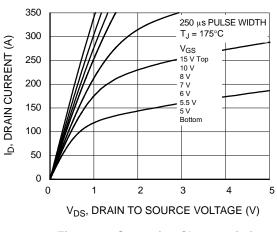
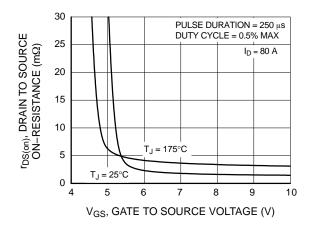


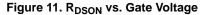
Figure 8. Forward Diode Characteristics





#### TYPICAL CHARACTERISTICS (CONTINUED)





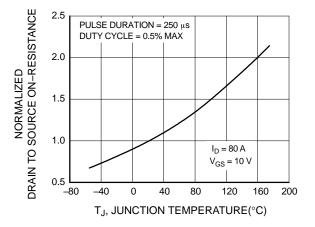


Figure 12. Normalized R<sub>DSON</sub> vs. Junction Temperature

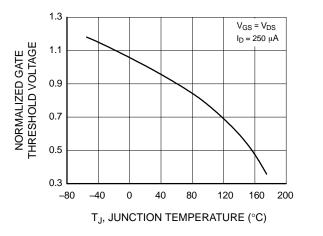
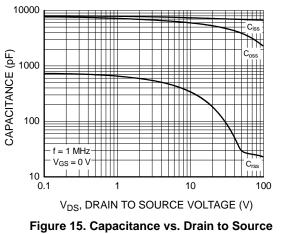


Figure 13. Normalized Gate Threshold Voltage vs. Temperature



apacitance vs. Dra Voltage

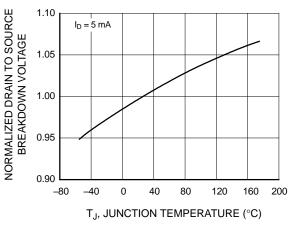
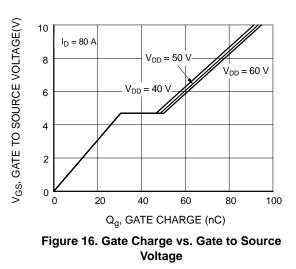
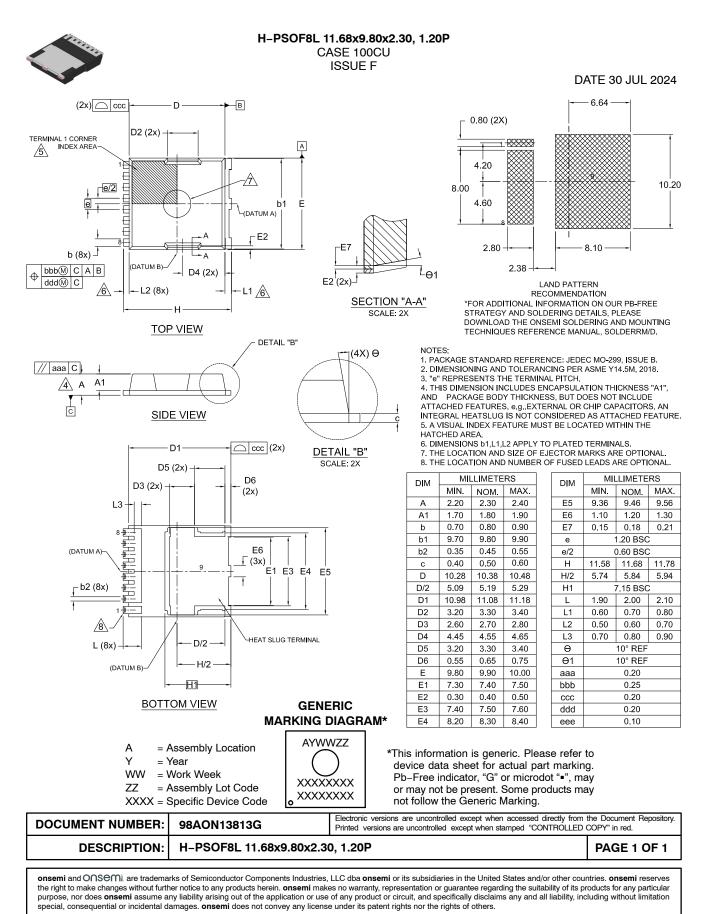


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature



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